

MOSFETs Silicon N-channel MOS (U-MOS<sup>VI</sup>-H)

# TPH2R608NH

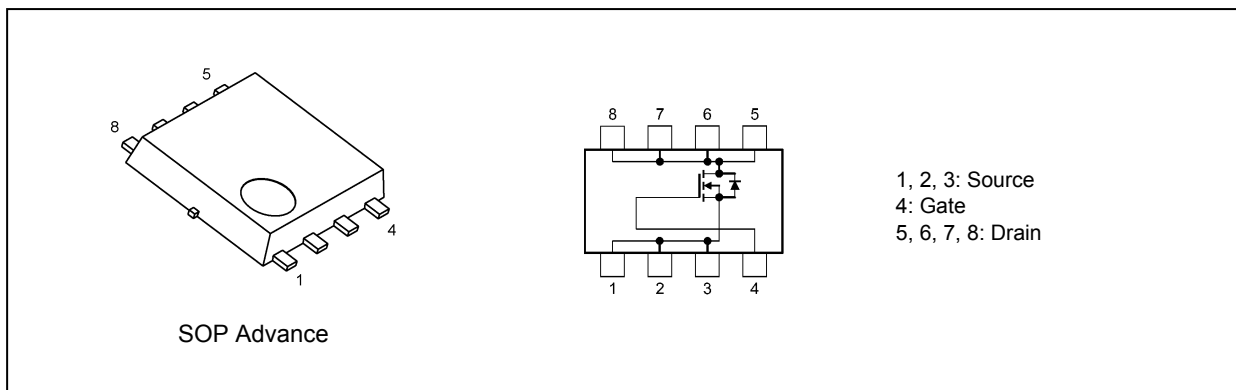
### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 28 \text{ nC}$  (typ.)
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 2.1 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 75 \text{ V}$ )
- (5) Enhancement mode:  $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1.0 \text{ mA}$ )

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	75	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	
Drain current (DC) (Note 1)	$I_D$	150	A
Drain current (DC) (Silicon limit) (Note 1), (Note 2)	$I_D$	168	A
Drain current (pulsed) ( $t = 100 \text{ }\mu\text{s}$ ) (Note 1)	$I_{DP}$	500	A
Power dissipation ( $T_c = 25 \text{ }^\circ\text{C}$ )	$P_D$	142	W
Power dissipation (Note 3)	$P_D$	2.5	W
Power dissipation (Note 4)	$P_D$	0.8	W
Single-pulse avalanche energy (Note 5)	$E_{AS}$	149	mJ
Single-pulse avalanche current (Note 5)	$I_{AS}$	120	A
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production  
2014-12

### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance ( $T_c = 25\text{ }^\circ\text{C}$ )	$R_{th(ch-c)}$	0.88	$^\circ\text{C}/\text{W}$
Channel-to-ambient thermal resistance ( $T_a = 25\text{ }^\circ\text{C}$ ) (Note 3)	$R_{th(ch-a)}$	50	
Channel-to-ambient thermal resistance ( $T_a = 25\text{ }^\circ\text{C}$ ) (Note 4)	$R_{th(ch-a)}$	156	

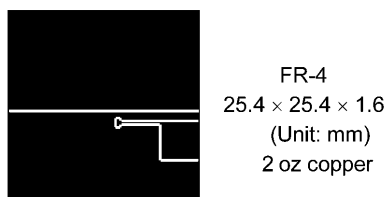
Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

Note 2: Limited by package limit. Silicon chip capability is 168 A. ( $T_c = 25\text{ }^\circ\text{C}$ )

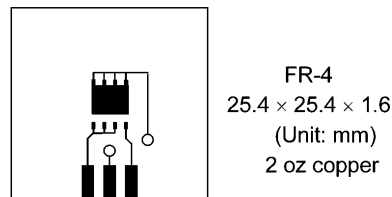
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD} = 60\text{ V}$ ,  $T_{ch} = 25\text{ }^\circ\text{C}$  (initial),  $L = 0.008\text{ mH}$ ,  $I_{AS} = 120\text{ A}$



**Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)**



**Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)**

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

#### 6.1. Static Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 0.1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	75	—	—	V
	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	55	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1.0\text{ mA}$	2.0	—	4.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$	—	2.1	2.6	$\text{m}\Omega$

#### 6.2. Dynamic Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 37.5\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	4600	6000	$\mu\text{F}$
Reverse transfer capacitance	$C_{rss}$		—	50	95	
Output capacitance	$C_{oss}$		—	1100	—	
Gate resistance	$r_g$	—	—	1.0	1.5	$\Omega$
Switching time (rise time)	$t_r$	See Fig. 6.2.1	—	11	—	ns
Switching time (turn-on time)	$t_{on}$		—	30	—	
Switching time (fall time)	$t_f$		—	15	—	
Switching time (turn-off time)	$t_{off}$		—	56	—	

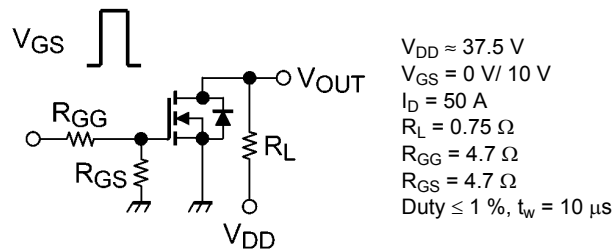


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 37.5\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$	—	72	—	nC
Gate-source charge 1	$Q_{gs1}$		—	24	—	
Gate-drain charge	$Q_{gd}$		—	18	—	
Gate switch charge	$Q_{SW}$		—	28	—	

#### 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 6)	$I_{DRP}$ ( $t = 100\ \mu\text{s}$ )	—	—	—	500	A
Diode forward voltage	$V_{DSF}$	$I_{DR} = 150\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V

Note 6: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

7. Marking

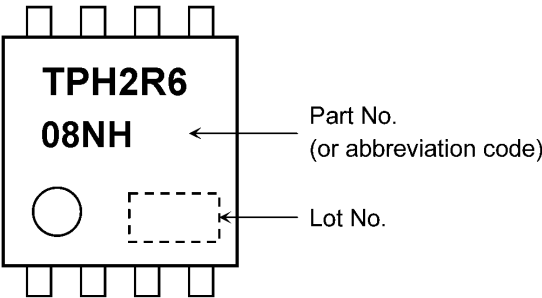
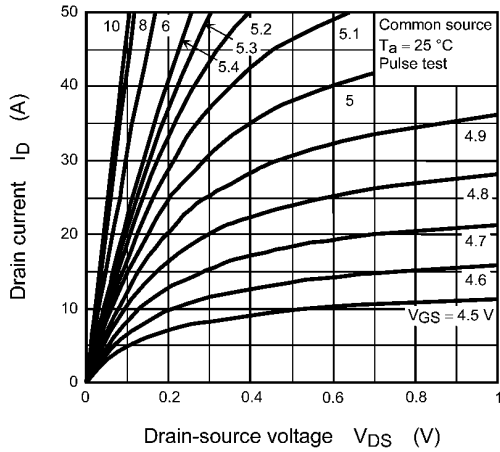
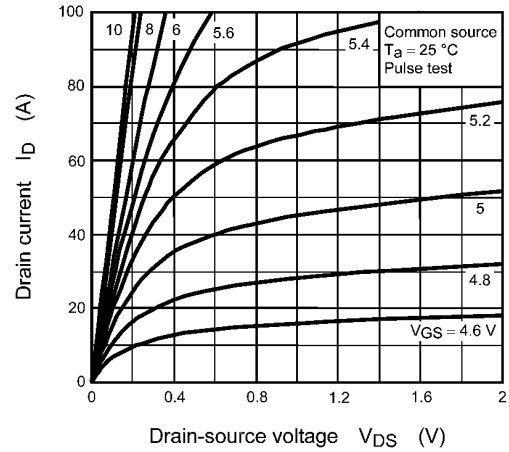


Fig. 7.1 Marking

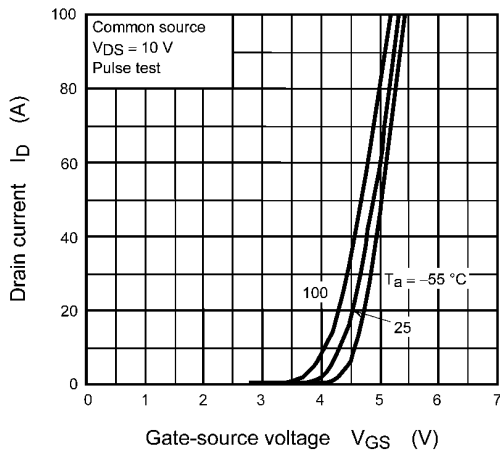
### 8. Characteristics Curves (Note)



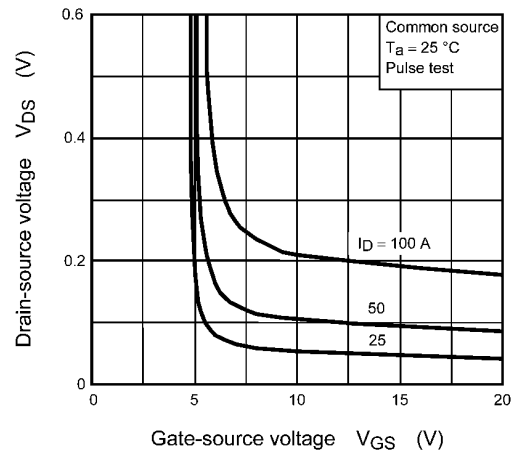
**Fig. 8.1  $I_D - V_{DS}$**



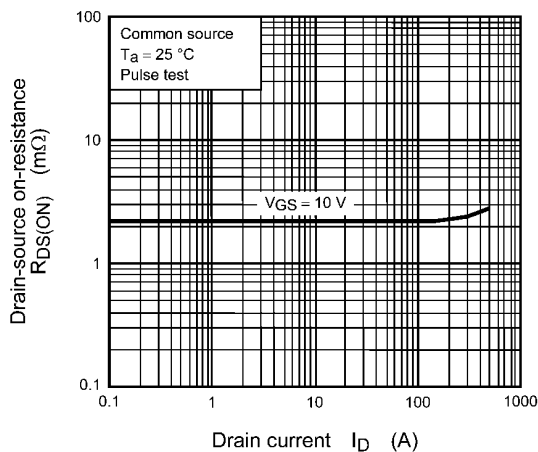
**Fig. 8.2  $I_D - V_{DS}$**



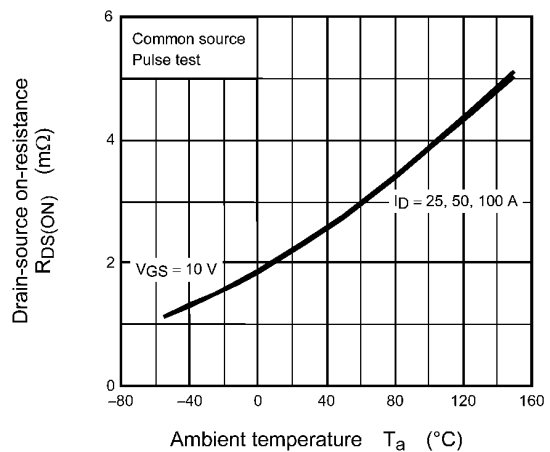
**Fig. 8.3  $I_D - V_{GS}$**



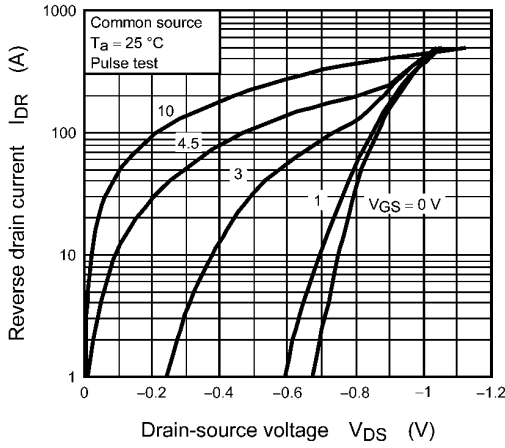
**Fig. 8.4  $V_{DS} - V_{GS}$**



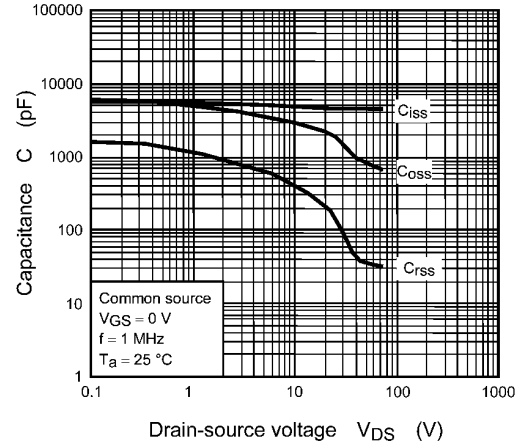
**Fig. 8.5  $R_{DS(ON)} - I_D$**



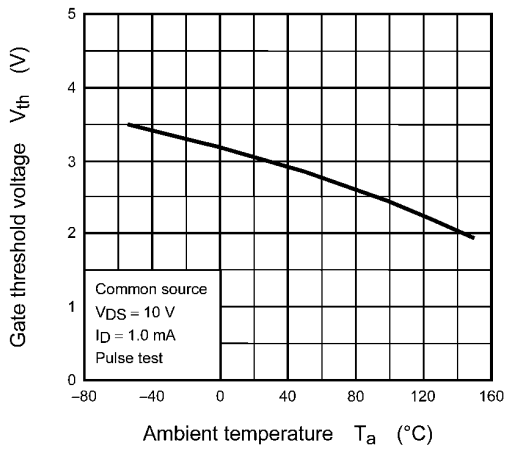
**Fig. 8.6  $R_{DS(ON)} - T_a$**



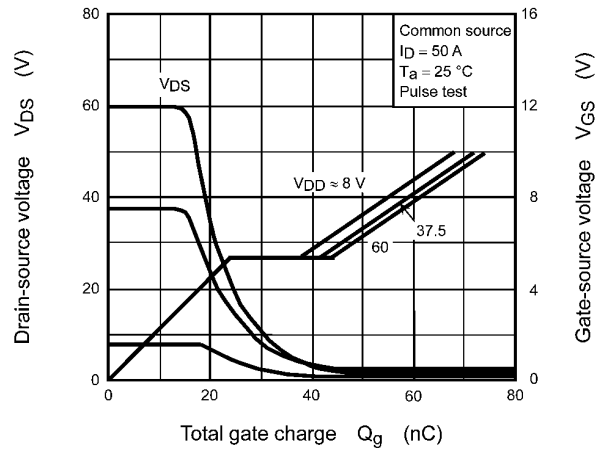
**Fig. 8.7  $I_{DR} - V_{DS}$**



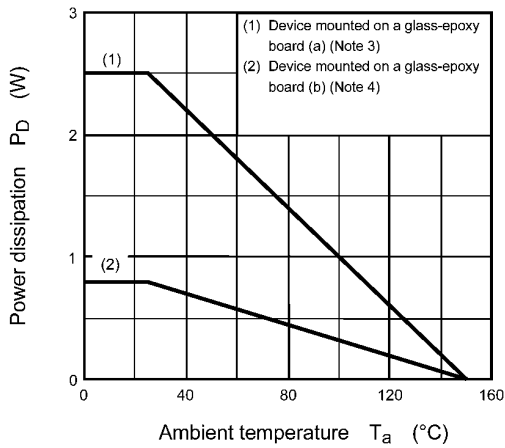
**Fig. 8.8 Capacitance -  $V_{DS}$**



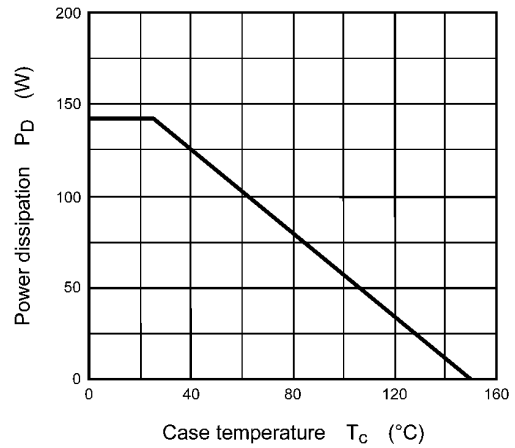
**Fig. 8.9  $V_{th} - T_a$**



**Fig. 8.10 Dynamic Input/Output Characteristics**



**Fig. 8.11  $P_D - T_a$   
(Guaranteed Maximum)**



**Fig. 8.12  $P_D - T_c$   
(Guaranteed Maximum)**

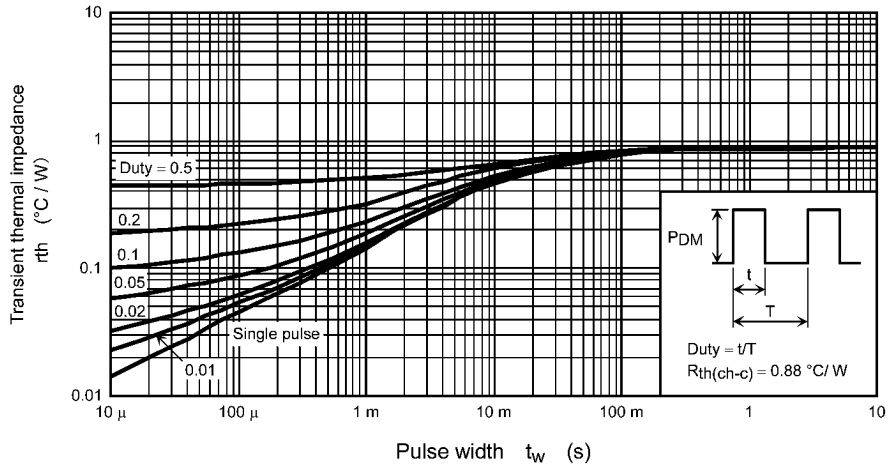


Fig. 8.13  $r_{th} - t_w$   
(Guaranteed Maximum)

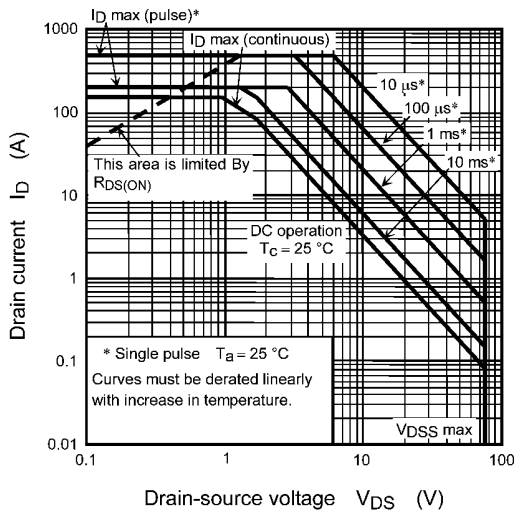
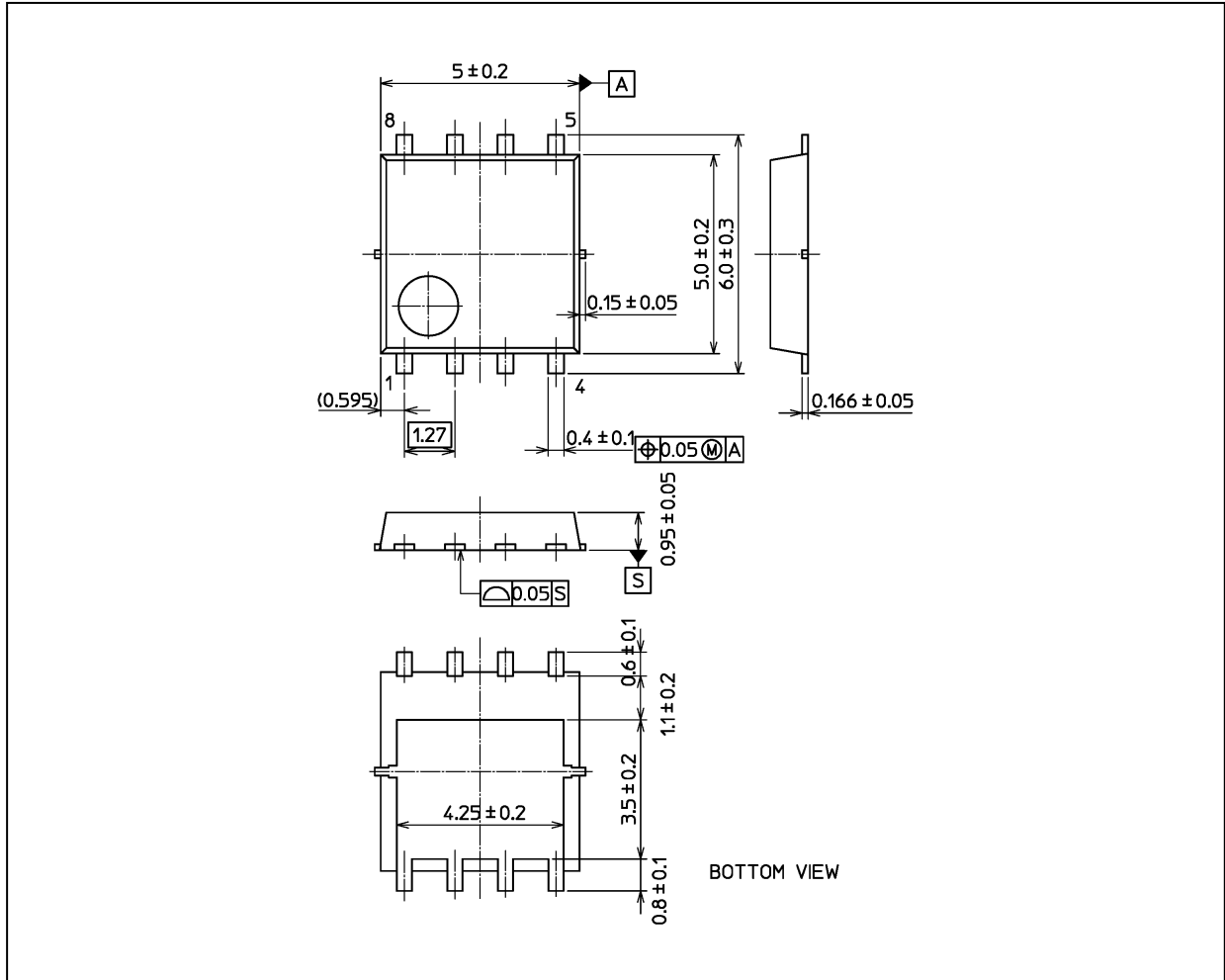


Fig. 8.14 Safe Operating Area  
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.087 g (typ.)

Package Name(s)
TOSHIBA: 2-5Q1S
Nickname: SOP Advance

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